TECHSEM

Y50ZPD
RECTIFIER DIODE

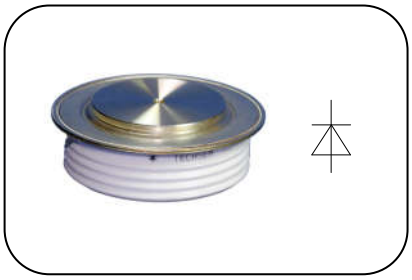
Features

- Low forward voltage drop
- High reverse voltage
- Hermetic metal cases with ceramic insulators

Typical Applications

- All purpose high power rectifier diodes
- High power resistance welding equipment
- Non-controllable and half-controllable rectifiers
- Controlled rectifiers

$I_{F(AV)}$	1980 A
V_{RRM}	2100~3000 V
I_{FSM}	27 kA
I^2t	3645 10^3A^2S



SYMBOL	CHARACTERISTIC	TEST CONDITIONS		T_j(°C)	VALUE			UNIT
					Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Double side cooled,	T_C=85°C	160			1980	A
V_{RRM}	Repetitive peak reverse voltage	tp=10ms		160	2100		3000	V
I_{RRM}	Repetitive peak current	At V_{RRM}		160			80	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}		160			27	kA
I^2t	I^2t for fusing coordination						3645	A^2s*10^3
V_{FO}	Threshold voltage			160			0.82	V
r_F	Forward slope resistance						0.22	mΩ
V_{FM}	Peak forward voltage	I_{FM}=3000A, F=24kN		25			2.00	V
Q_{rr}	Recovery charge	I_{FM}=2000A, tp=2000μs, di/dt=-20A/μs, V_R=50V		160		3500		μC
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180^0 sine, double side cooled Clamping force 24kN					0.020	°C /W
$R_{th(c-h)}$	Thermal resistance case to heat sink						0.005	
F_m	Mounting force				19		26	kN
T_{stg}	Stored temperature				-40		160	°C
W_t	Weight					440		g
Outline	ZT50cT							

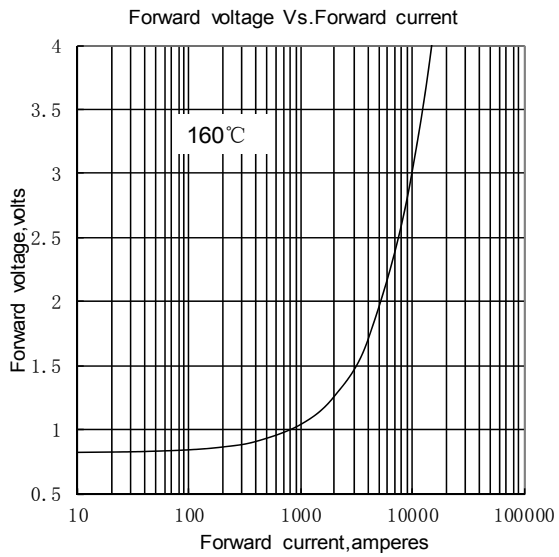


Fig.1

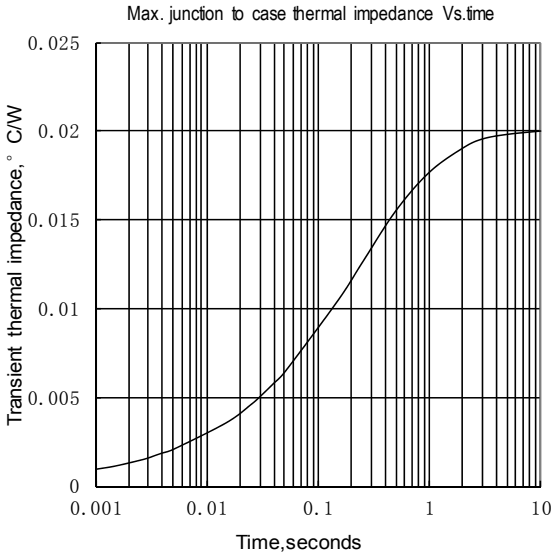


Fig.2

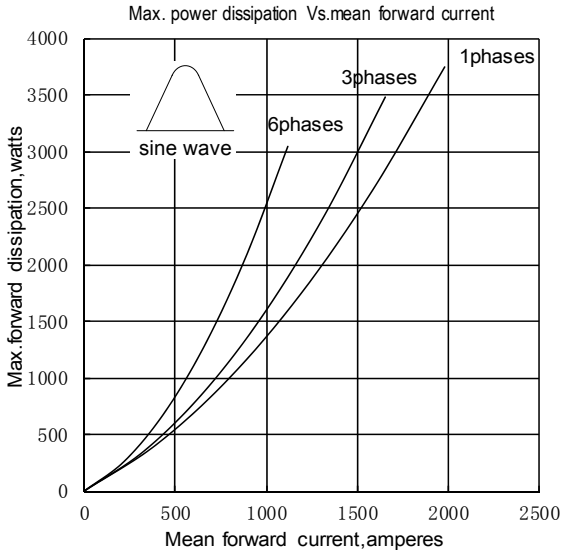


Fig.3

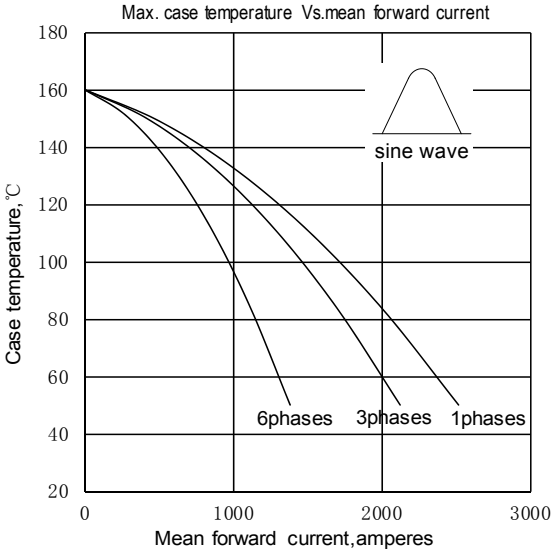


Fig.4

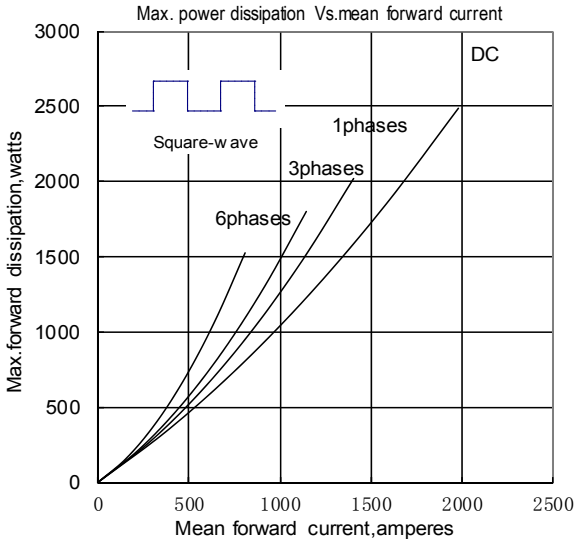


Fig.5

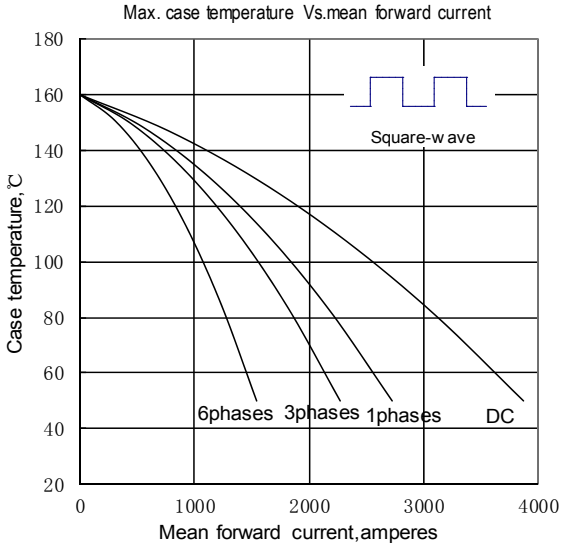


Fig.6

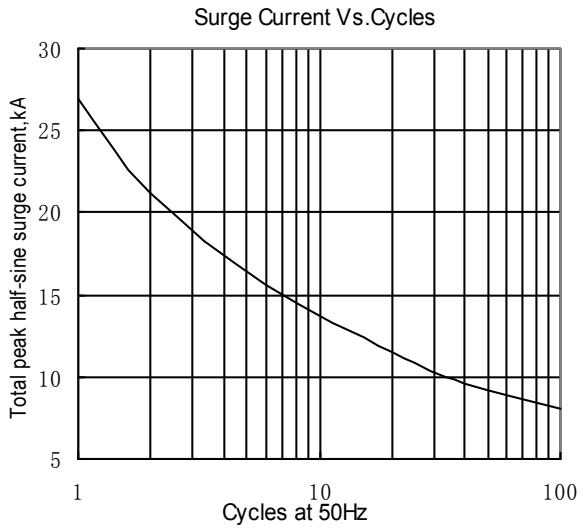


Fig.7

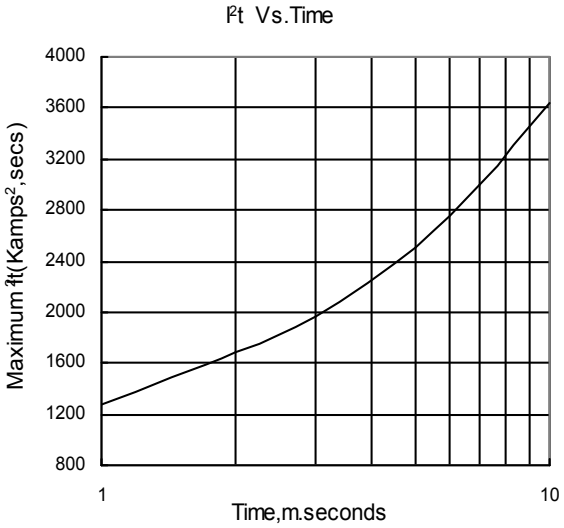


Fig.8

Outline: